

P-CHANNEL SILICON POWER MOSFET

FAP-III SERIES

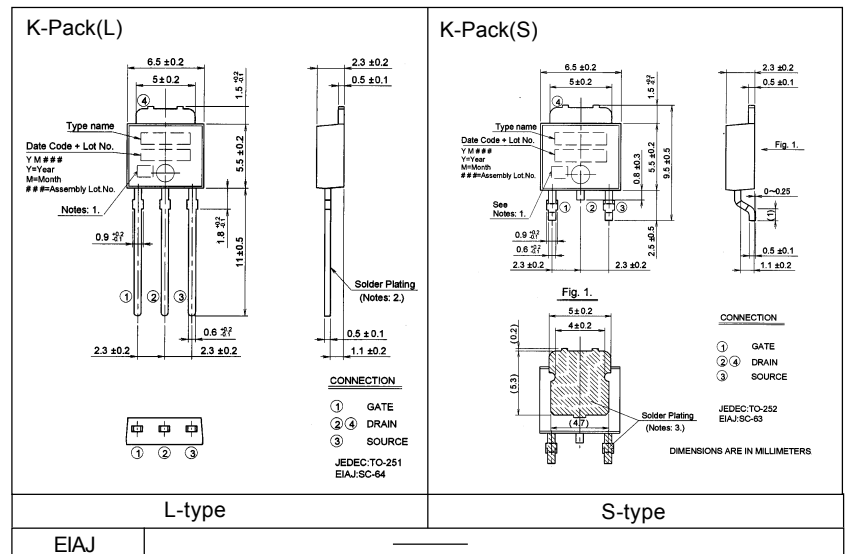
Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- High forward Transconductance
- Avalanche-proof

Applications

- Switching regulators
- DC-DC converters
- General purpose power amplifier

Outline Drawings



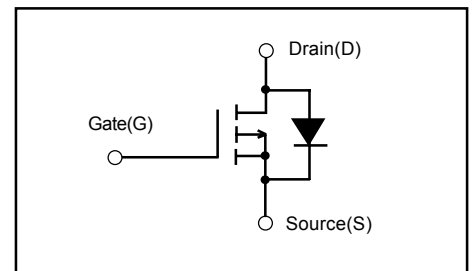
Maximum ratings and characteristics

Absolute maximum ratings (Tc=25°C unless otherwise specified)

Item	Symbol	Rating	Unit
Drain-source voltage	V _{DS}	-30	V
Continuous drain current	I _D	±5	A
Pulsed drain current	I _D (puls)	±20	A
Gate-source voltage	V _{GS}	±16	V
Maximum avalanche energy *1	E _{AV}	191.8	V
Maximum power dissipation(Tc=25°C)	P _D	15	W
Operating and storage temperature range	T _{ch} T _{stg}	+150 -55 to +150	°C

*1 L=10.23mH, V_{CC}= -12V

Equivalent circuit schematic



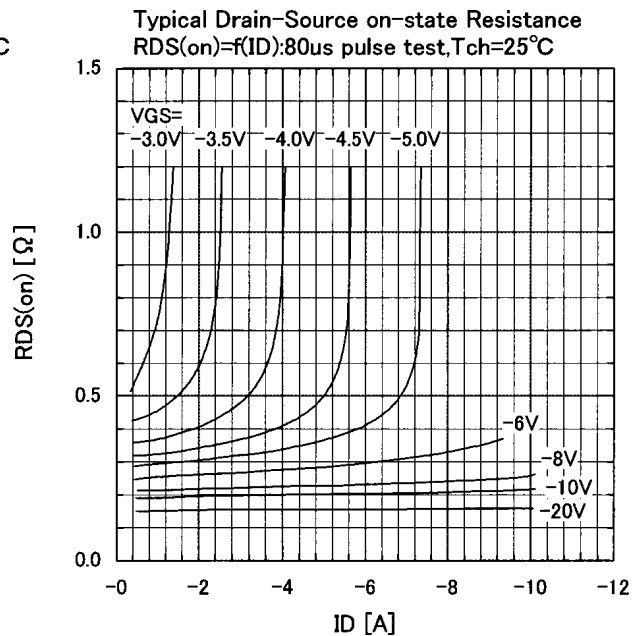
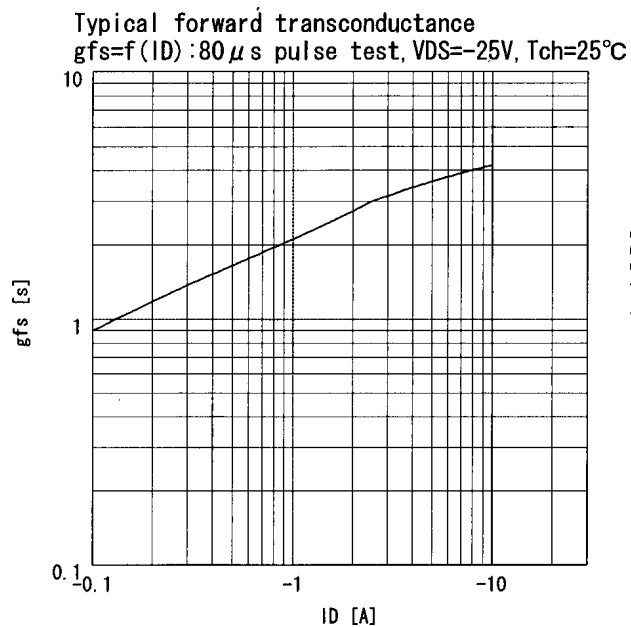
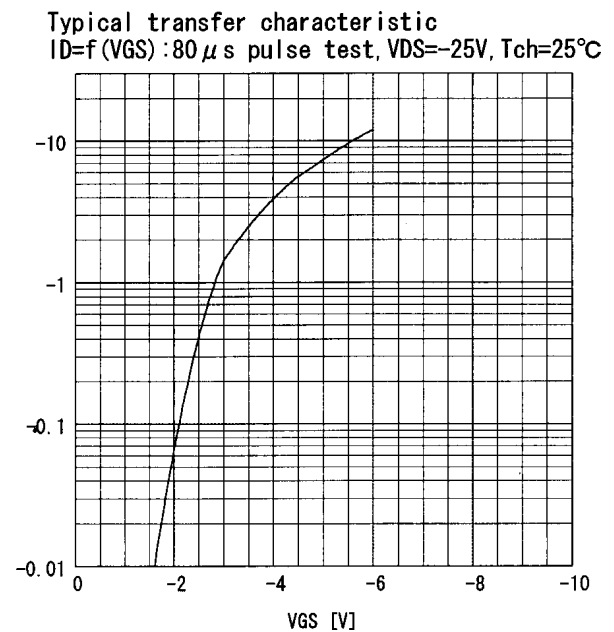
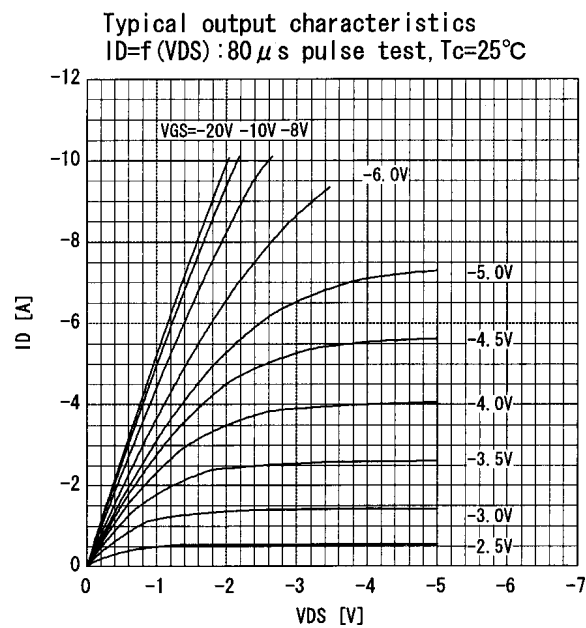
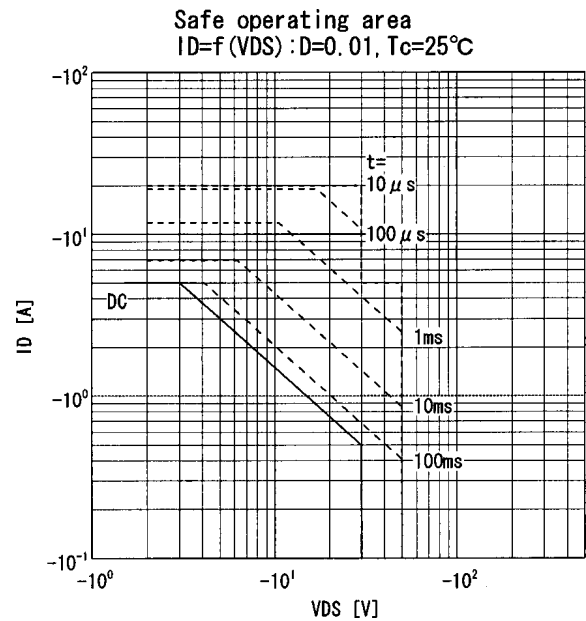
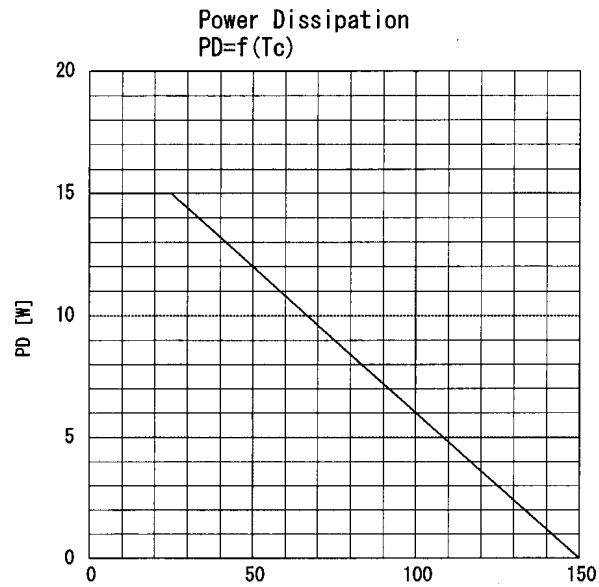
Electrical characteristics (Tc =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	BV _{DSS}	I _D =1mA V _{GS} =0V	-30			V
Gate threshold voltage	V _{GS(th)}	I _D =1mA V _{DS} =V _{GS}	-1.0	-1.5	-2.5	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -30V T _{ch} =25°C		-10	-500	μA
		V _{GS} =0V T _{ch} =125°C		-0.2	-1.0	mA
Gate-source leakage current	I _{GSS}	V _{GS} =±16V V _{DS} =0V		10	100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D = -2.5A V _{GS} = -4V		480	850	mΩ
		V _{GS} = -10V		210	400	mΩ
Forward transconductance	g _{fs}	I _D =2.5A V _{DS} = -25V	1.5	3.0		S
Input capacitance	C _{iss}	V _{DS} = -25V		250	380	pF
Output capacitance	C _{oss}	V _{GS} =0V		150	230	pF
Reverse transfer capacitance	C _{rss}	f=1MHz		85	130	pF
Turn-on time	td(on)	V _{CC} = -12V R _G =10 Ω		10	15	ns
	t _r	I _D = -5A		20	30	ns
Turn-off time	td(off)	V _{GS} = -10V		25	40	ns
	t _f			20	30	ns
Avalanche capability	I _{AV}	L=100μH T _{ch} =25°C	-5			A
Diode forward on-voltage	V _{SD}	I _F =2I _{DR} V _{GS} =0V T _{ch} =25°C		-2.50	-3.8	V
Reverse recovery time	t _{rr}	I _F =I _{DR} V _{GS} =0V		90		ns
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		0.30		μC

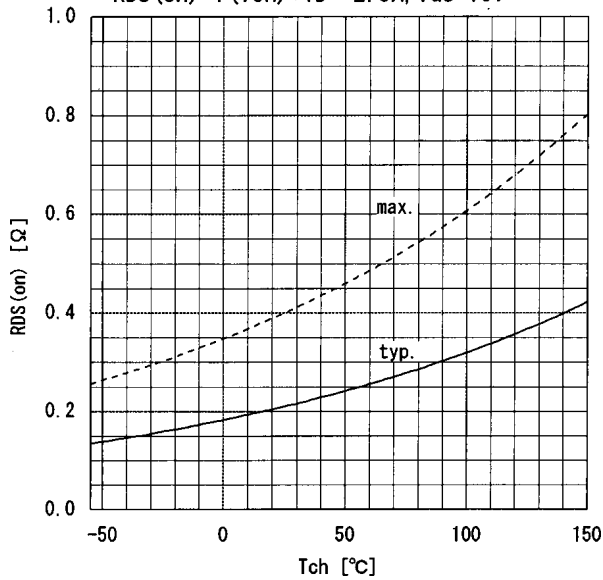
Thermal characteristics

Item	Symbol	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}			8.33	°C/W
	R _{th(ch-a)}			125.0	°C/W

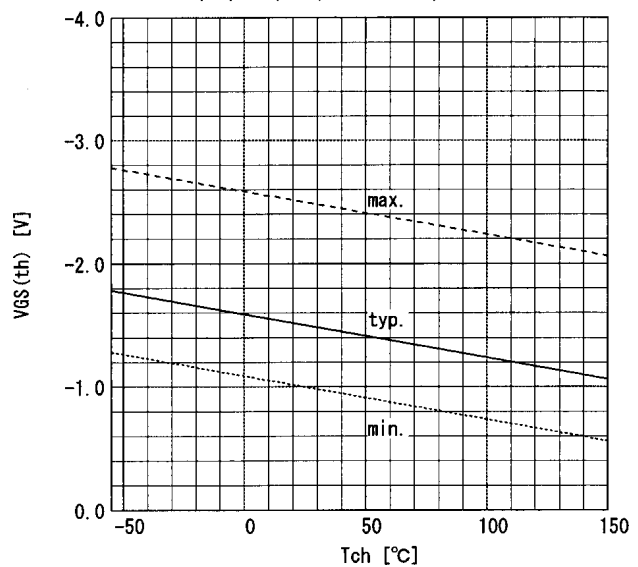
Characteristics



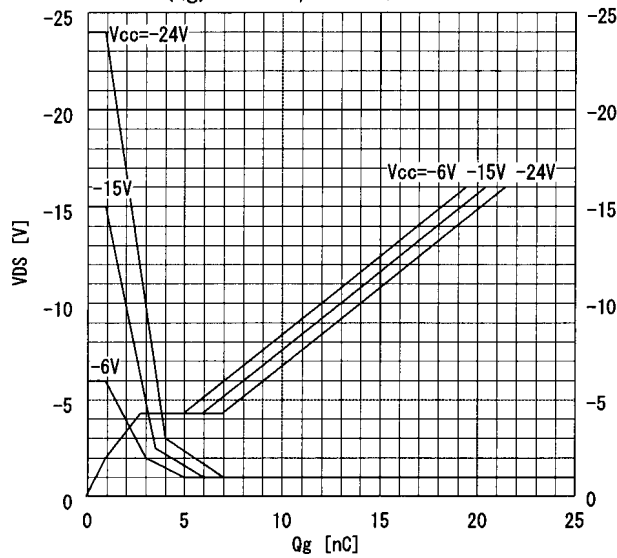
Drain-source on-state resistance
 $R_{DS(on)} = f(T_{ch}) : I_D = -2.5A, V_{GS} = 10V$



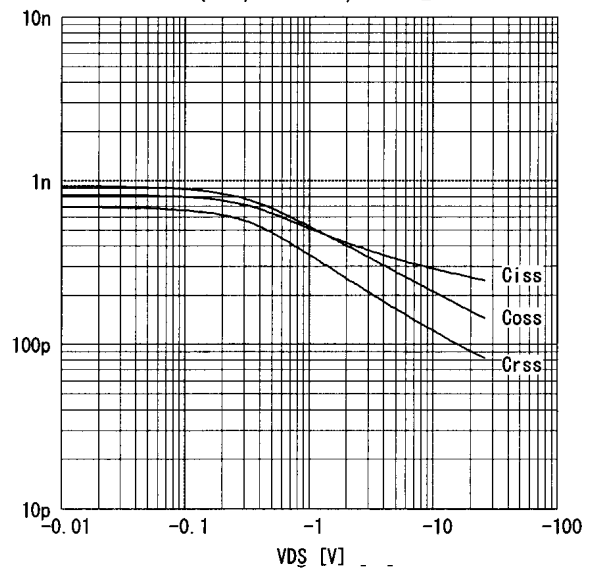
Gate threshold voltage
 $V_{GS(th)} = f(T_{ch}) : I_D = -1mA, V_{DS} = V_{GS}$



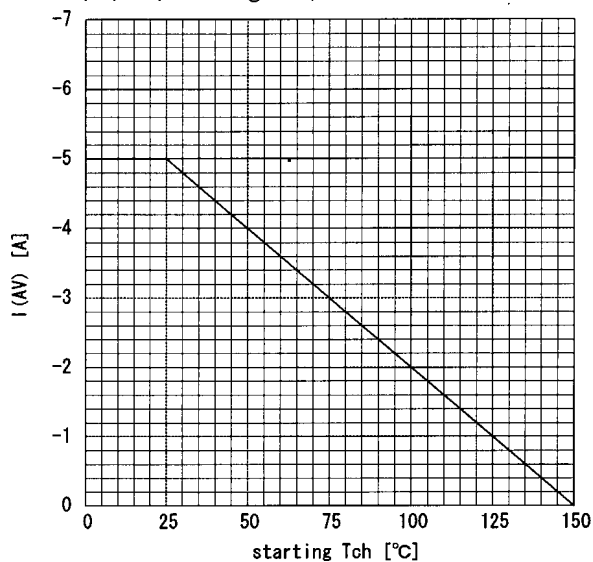
Typical gate charge characteristic
 $V_{GS} = f(Q_g) : I_D = -5A, T_c = 25°C$



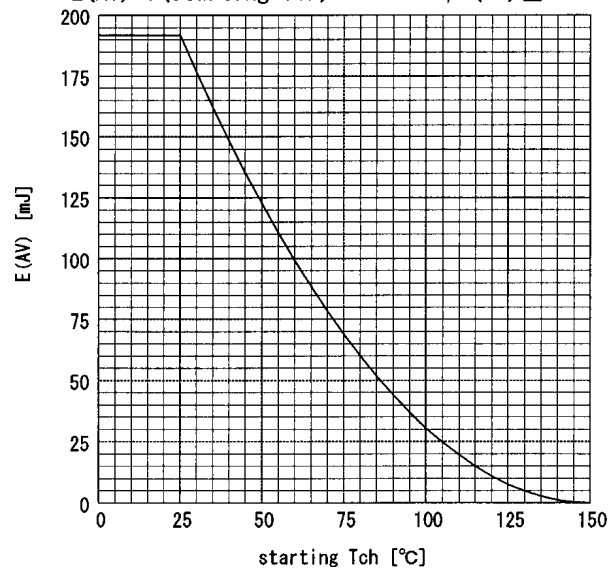
Typical capacitances
 $C = f(V_{DS}) : V_{GS} = 0V, f = 1MHz$



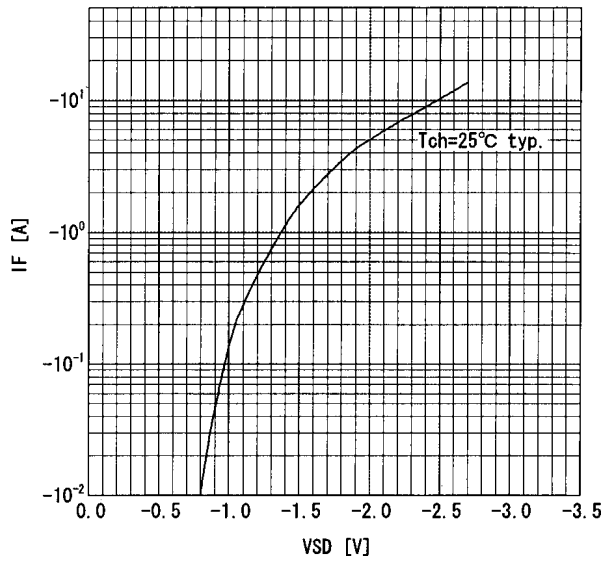
Maximum Avalanche Current vs. starting T_{ch}
 $I(AV) = f(\text{starting } T_{ch})$



Maximum Avalanche Energy vs. starting T_{ch}
 $E(AV) = f(\text{starting } T_{ch}) : V_{CC} = -12V, I(AV) \geq -5A$



Forward characteristic of reverse of diode
 $I_F = f(V_{SD}) : 80 \mu s$ pulses test, $V_{GS} = 0V$



Transient thermal impedance
 $Z_{thch} = f(t)$ parameter: $D = t/T$

